Seat No.:	Enrolment No.

GUJARAT TECHNOLOGICAL UNIVERSITY

PDDC - SEMESTER-I • EXAMINATION - WINTER 2013

Su	bject	Code: X11101 Date: 21-12-2013	
Su	bject	Name: Basic Electronics	
		0.30 am - 01.00 pm Total Marks: 70	
Inst	2.	Attempt all questions. Make suitable assumptions wherever necessary. Figures to the right indicate full marks.	
Q.1	(a)	Define following terms: 1. Electron Volt 2. Photo ionization 3. Photo excitation 4. Mean lifetime of a carrier 5. Mass action law 6. Intrinsic semiconductor 7. Extrinsic semiconductor	07
	(b)	Write short note: Potential Energy Barrier between two electrodes.	07
Q.2	(a) (b)	Explain Hall Effect. Derive expression of Hall voltage and state its applications. A 1mm long bar of silicon is doped with donor impurity of $5x10^{10}$ / cm ³ . Find the voltage drop across the bar if the current density within the bar is 1mA / cm ² . Given : for Si at 300^0 K, n_i =1.5x10 ¹⁰ /cm ³ , μ_n =1300cm ² /V-sec, μ_p =500 cm ² /V-sec.	07 07
	(b)	Derive expression for Continuity Equation.	07
Q.3	(a) (b)	What is Transition Capacitance? Derive its expression with suitable diagram. Derive expression for diode Static and Dynamic resistance. OR	07 07
Q.3	(a) (b)	Explain construction, working and application of Varactor Diode. With suitable waveforms explain Junction Diode Switching Time.	07 07
Q.4	(a) (b)	Write principle and application of Light Emitting Diode. Explain the h-parameter model of CE amplifier with bypass resistance R_E and derive expression for A_i , A_v , R_i and R_o . OR	07 07
Q.4	(a) (b)	Explain input and output characteristics of CB configuration of Transistor. Explain the operation of Fixed Bias circuit.	07 07
Q.5	(a) (b)	List out Bias Compensation techniques. Explain any three in detail. Give construction details of JFET and draw and explain its characteristics.	07 07
Q.5	(a) (b)	OR Give comparisons between JFET & MOSFET. Explain class A Push Pull Amplifier.	07 07
